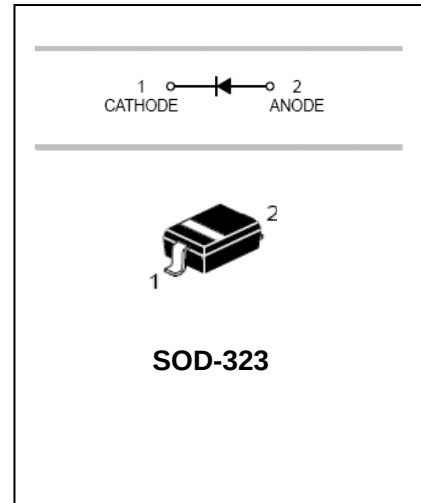


Silicon Epitaxial Planar Diode**BAS316****FEATURES**

- Very small plastic SMD package.
- High switching speed:max.4ns
- Continuous reverse voltage:max.100v
- Repetitive peak reverse voltage:max.100v
- Repetitive peak forward current:max.500mA



Lead-free

**APPLICATIONS**

- Surface mount fast switching diode

ORDERING INFORMATION

Type No.	Marking	Package Code
BAS316	A6	SOD-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
DC Reverse Voltage	V_R	100	V
Forward Current	I_F	300	mA
Power Dissipation	P_d	200	mW
Junction and Storage Temperature Range	T_j, T_{STG}	-65 to +150	°C

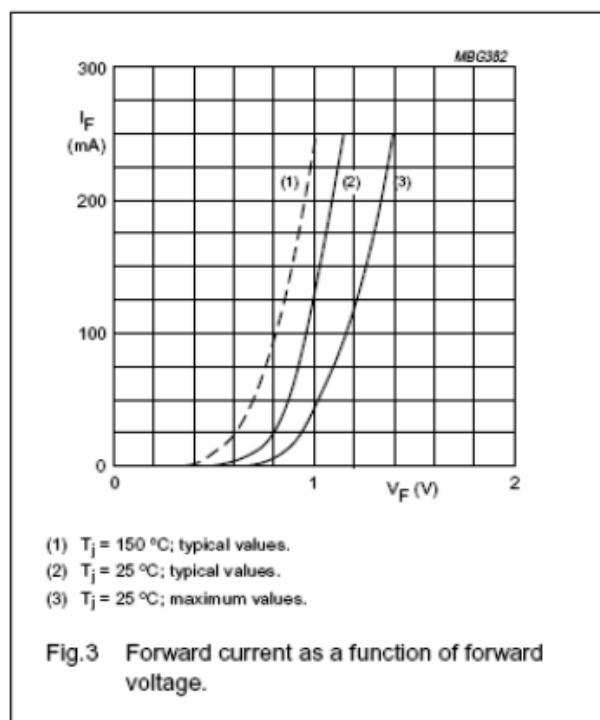
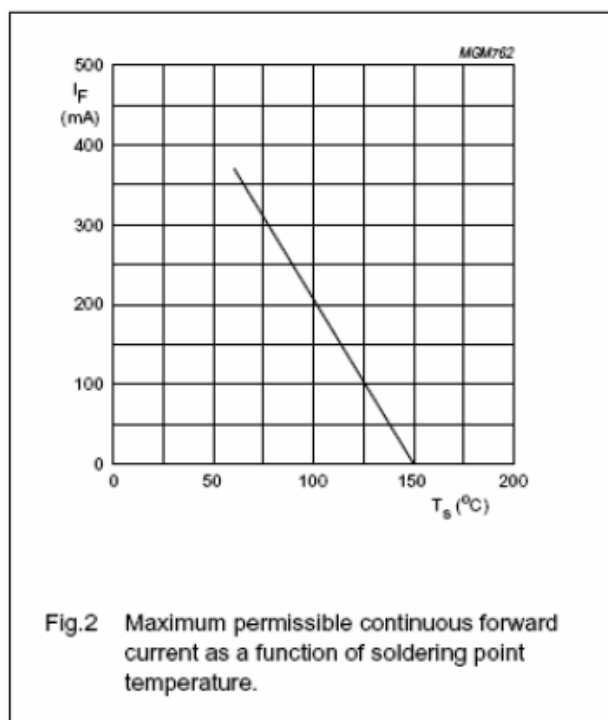
Silicon Epitaxial Planar Diode

BAS316

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

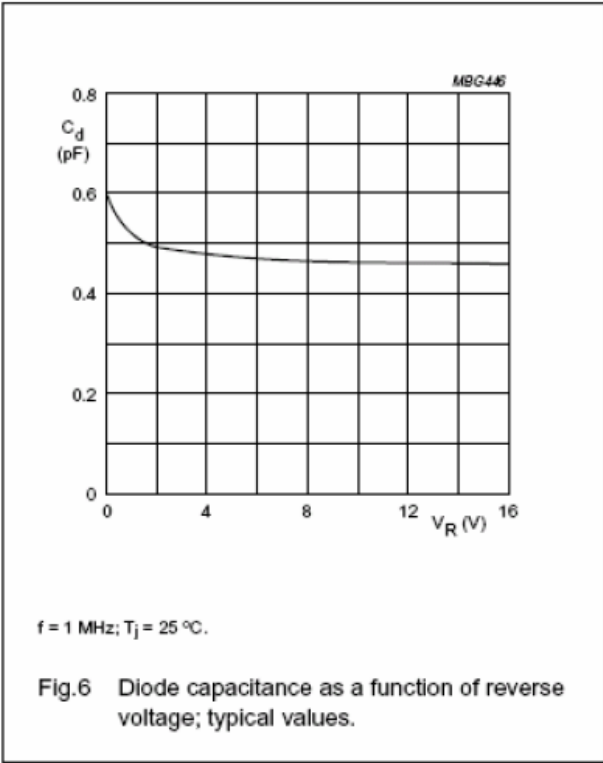
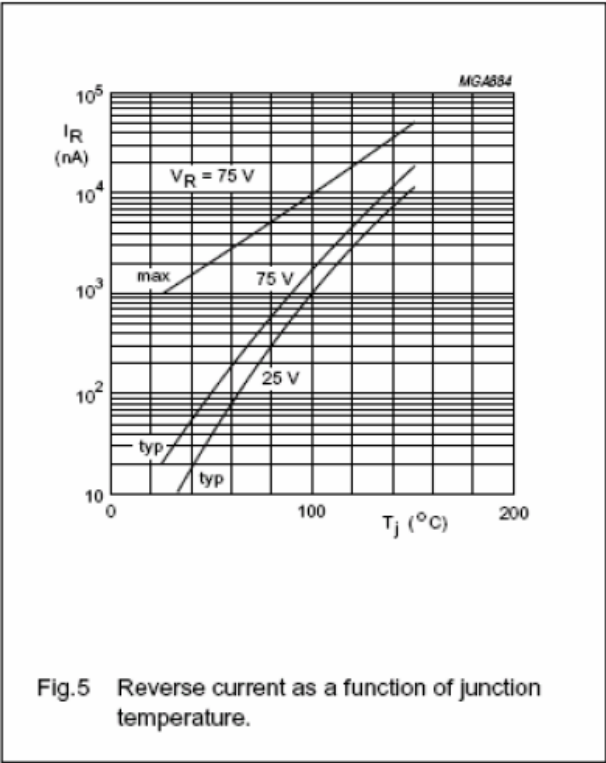
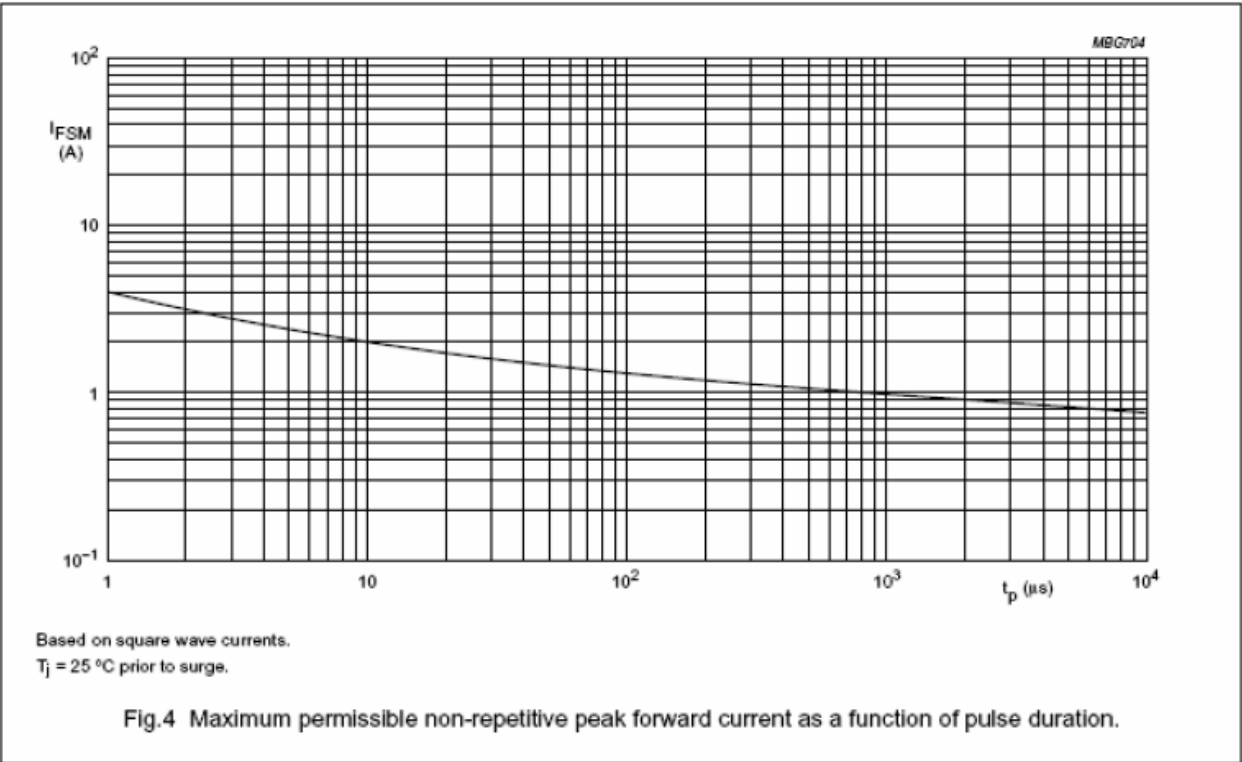
Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	100	-	V	$I_R=100\mu\text{A}$
Forward Voltage	V_F	0.62	0.715 0.855 1.0 1.25	V	$I_F=1.0\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$
Reverse Current	I_R	-	1.0 0.03	μA	$V_R=75\text{V}$ $V_R=25\text{V}$
Capacitance between terminals	C_T	-	1.5	pF	$V_R=0, f=1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	-	4.0	ns	$I_F=I_R=10\text{mA}, R_L=100\Omega$

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



Silicon Epitaxial Planar Diode

BAS316



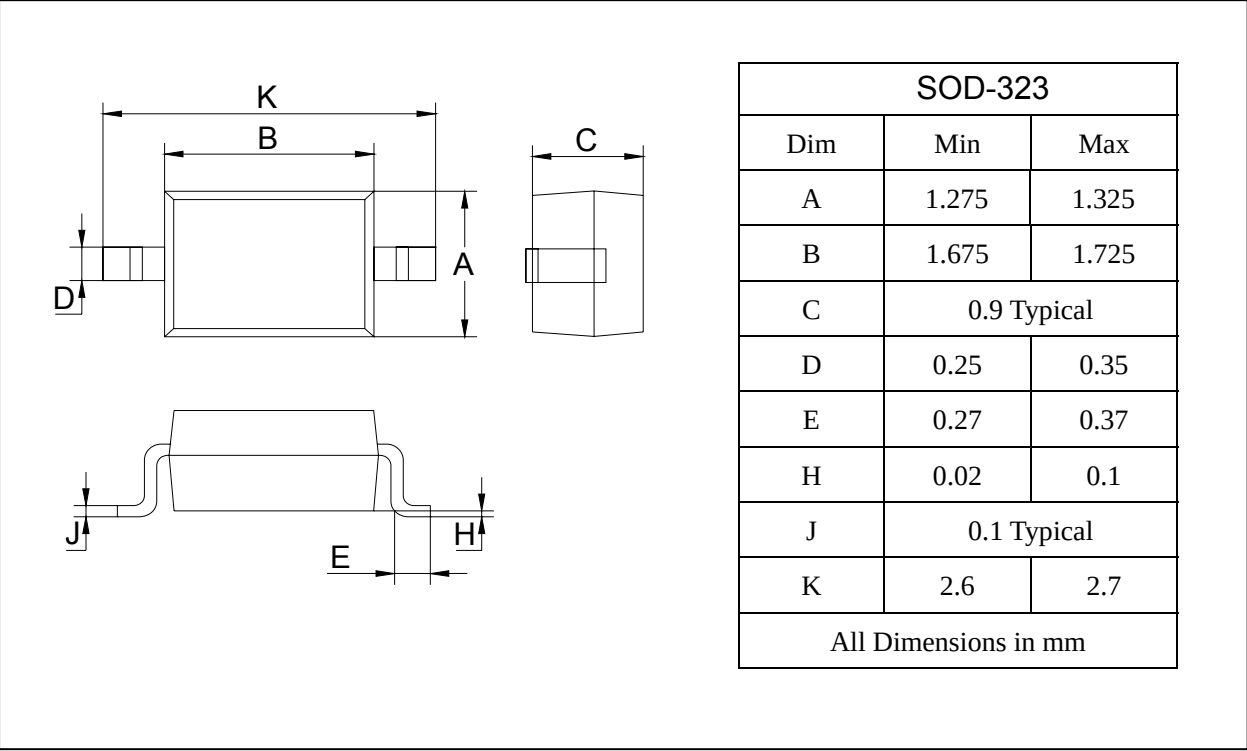
Silicon Epitaxial Planar Diode

BAS316

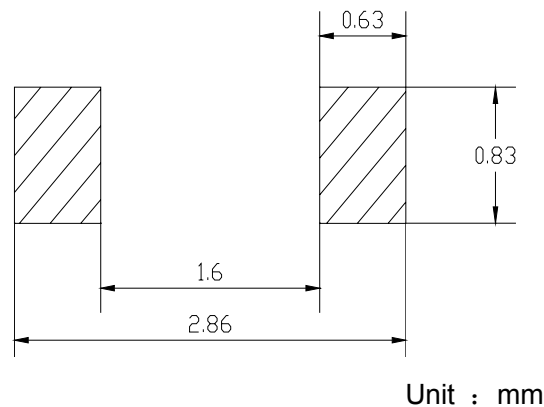
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAS316	SOD-323	3000/Tape&Reel